

N-channel 100 V, 21 mΩ logic level MOSFET in LFPAK56

4 November 2016

Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

#### Features and benefits 2.

- Advanced TrenchMOS provides low R<sub>DSon</sub> and low gate charge •
- Logic level gate operation
- Avalanche rated, 100 % tested •
- LFPAK provides maximum power density in a Power SO8 package

#### **Applications** 3.

- Synchronous rectification in power supply equipment
- Chargers & adaptors with  $V_{out}$  < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

### 4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	49	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	147	W
Static charac	teristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	17.4	22	mΩ
Dynamic cha	racteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	13.3	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFA
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering in	able 3. Ordering information							
Type number	Package							
	Name	Description	Version					
PSMN021-100YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669					

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN021-100YL	21L100

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mii	n Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	147	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	49	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	35	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3	-	197	А
T <sub>stg</sub>	storage temperature		-5	5 175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Т <sub>ј</sub>	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	49	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	197	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 49 \text{ A};  V_{sup} \leq 100  \text{V};  \text{R}_{GS} = 50  \Omega; \\ V_{GS} &= 5  \text{V};        $	[1][2]	-	80.8	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.

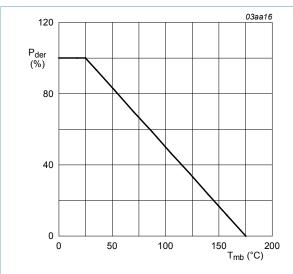


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

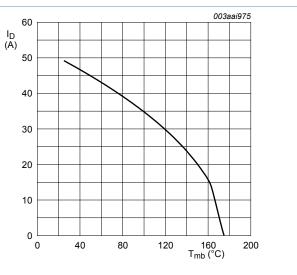
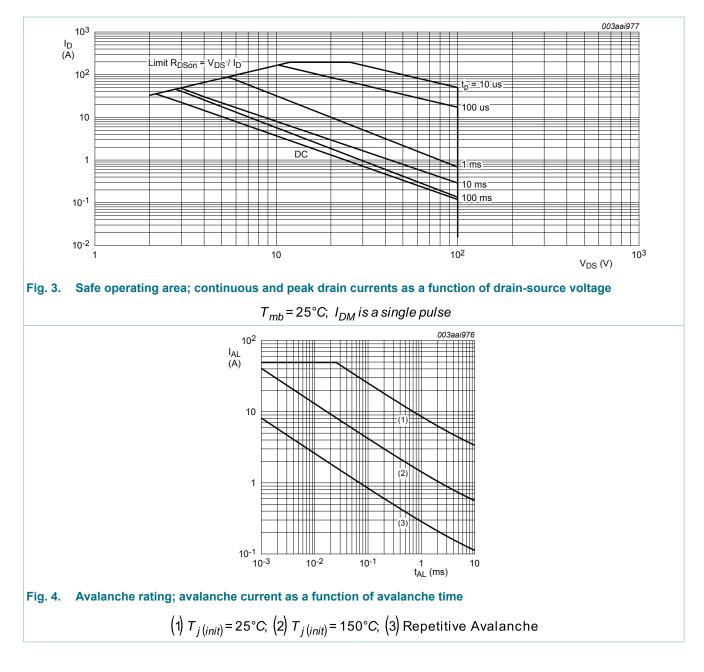


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$ 

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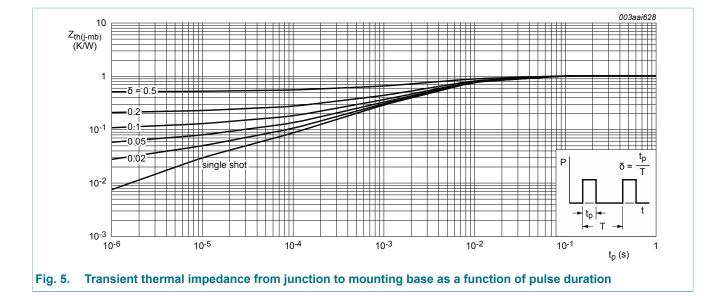
### 9. Thermal characteristics

Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.02	K/W

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### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub> gate-source thresho voltage	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA	
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.04	10	μA
I <sub>GSS</sub> gate I	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	17.4	22	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 11	-	16.8	21.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	60.7	mΩ
Dynamic cł	naracteristics	· · ·			_	
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 80 V; $V_{GS}$ = 10 V;	-	65.6	-	nC
		T <sub>j</sub> = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>				
		$I_D$ = 15 A; $V_{DS}$ = 80 V; $V_{GS}$ = 5 V;	-	35.8	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	6.2	-	nC

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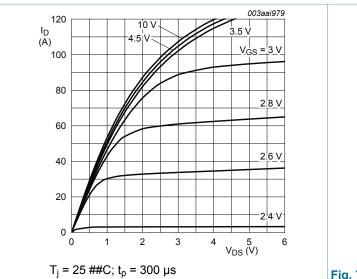
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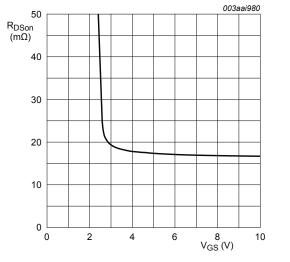
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>GD</sub>	gate-drain charge		-	13.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	3480	4640	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	 -	212	254	pF
C <sub>rss</sub>	reverse transfer capacitance		-	130	178	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 80 V; $R_{L}$ = 5 Ω; $V_{GS}$ = 5 V; $R_{G(ext)}$ = 5 Ω; $T_{j}$ = 25 °C	-	15.8	-	ns
t <sub>r</sub>	rise time		-	32.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		 -	53.4	-	ns
t <sub>f</sub>	fall time	_	-	31.1	-	ns
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 15 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;	-	37	-	ns

V<sub>DS</sub> = 25 V; T<sub>i</sub> = 25 °C



recovered charge





-

52

-

nC

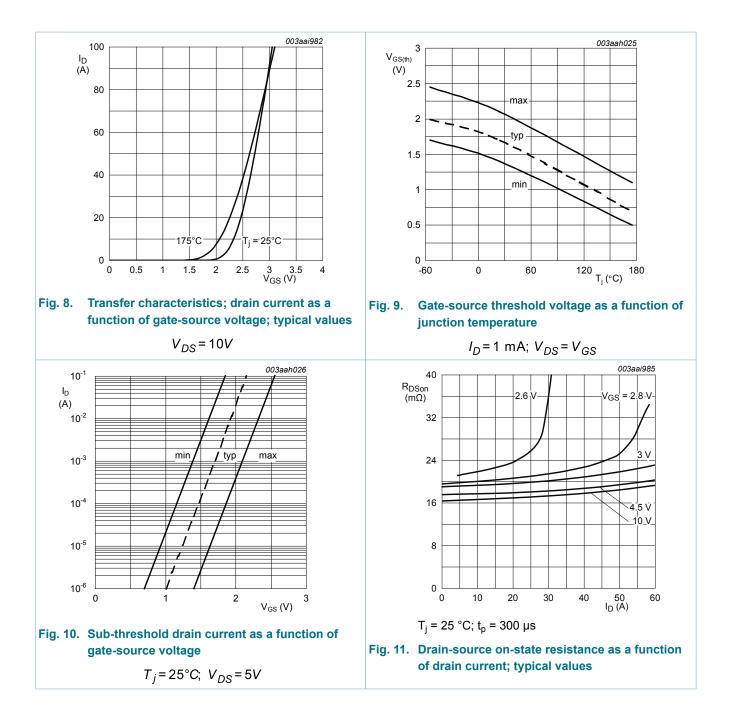
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 15A$ 

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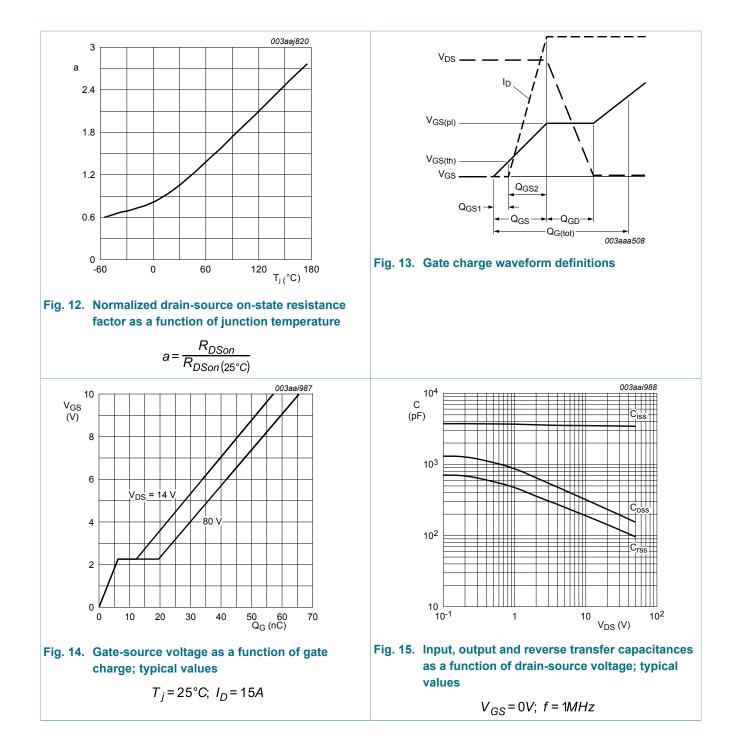
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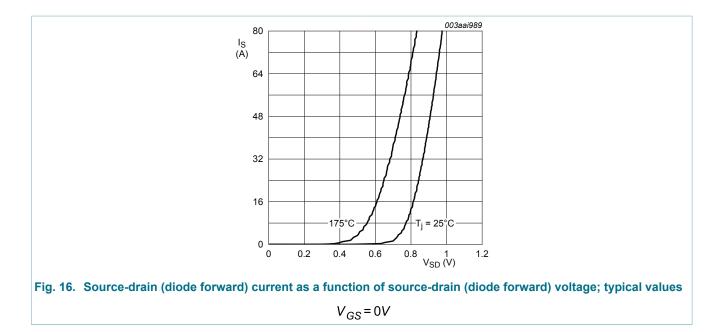
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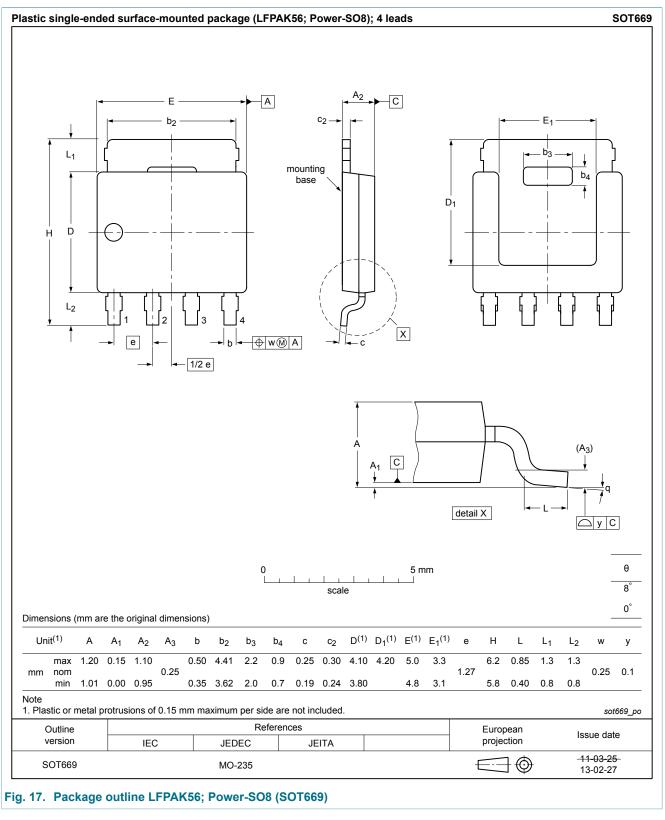
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#### N-channel 100 V, 21 m $\Omega$ logic level MOSFET in LFPAK56



#### N-channel 100 V, 21 mQ logic level MOSFET in LFPAK56

### 11. Package outline



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#### N-channel 100 V, 21 mΩ logic level MOSFET in LFPAK56

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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